Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S509	40	((buried adj (insulating or insulation or isolation or oxide)) with substrate with (distance or thickness or thick) with (angstrom or ang or nm or nanometers)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 18:13
S510	13	((buried adj (insulating or insulation or isolation or oxide)) with substrate with (distance or thickness or thick) with (angstrom or ang or nm or nanometers) with surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 18:14
S511	80	((buried adj (insulating or insulation or isolation or oxide)) with substrate with (distance or thickness or thick) with (angstrom or ang or nm or nanometers) with surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 18:16
S512	46	((buried adj (insulating or insulation or isolation or oxide)) near10 substrate near10 (distance or thickness or thick) near10 (angstrom or ang or nm or nanometers) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:38
S513	83	(depth or distance) near5 ((insulating or dielectric or oxide or dioxde or insulation or insulator) adj (layer or film)) near5 (thick or thickness) near5 substrate near5 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:43
S514	93	(depth or distance) near5 (buried (insulating or dielectric or oxide or dioxde or insulation or insulator) adj (layer or film)) near5 (thick or thickness) near5 substrate near5 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:43
S515	5	(depth or distance) near5 (buried near (insulating or dielectric or oxide or dioxde or insulation or insulator) adj (layer or film)) near5 (thick or thickness) near5 substrate near5 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:44
S516	12	(depth or distance) near10 (buried near (insulating or dielectric or oxide or dioxde or insulation or insulator) adj (layer or film)) near10 (thick or thickness) near10 substrate near10 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:47

S51 7	32	(depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:49
S51 8	12	(depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) and (substrate near5 (thick or thickness) near5 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:50
S51 9	11	(depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) and (substrate near5 (thick or thickness) near2 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:50
S52 0	3	(depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) and (substrate near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:51
S52 1	3	(depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:51
S52 2	9	((distance or depth) near2 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near2 (nm or nanometers or angstrom or ang) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:52

S52 3	20	(((distance or depth) near5 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) near5 surface) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:52
S52 4	11	(((distance or depth) near5 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) near5 surface near5 substrate) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:54
S52 5	7	(((distance or depth) near5 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near5 (nm or nanometers or angstrom or ang) near5 surface near5 substrate) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:54
S52 6	21	(((distance or depth) near5 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near5 (nm or nanometers or angstrom or ang) near5 surface near5 substrate) and ((wafer or substrate) near5 (thick or thickness) near5 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:55
S52 7	82	(((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near5 (thick or thickness) near5 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:56

S52 8	163	(((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near10 (thick or thickness) near10 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:56
S52 9	163	(((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near10 (thick or thickness) near10 (nanometer or nm or angstrom or ang)) and (((dielectric or insulation or insulating or oxide or dioxide or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:57
S53 0	151	(((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near10 (thick or thickness) near10 (nanometer or nm or angstrom or ang)) and (((dielectric or insulation or insulating or oxide or dioxide or insulator) near (layer or film)) near10 (thick or thickness) near5 (angstrom or ang or nanometer or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:00

S53 1	3	(((((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near10 (thick or thickness) near10 (nanometer or nm or angstrom or ang)) and (((dielectric or insulation or insulating or oxide or dioxide or insulator) near (layer or film)) near10 (thick or thickness) near5 (angstrom or ang or nanometer or nm))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 12:58
S53 2	4734	(buried adj (oxide or dioxide) adj (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:03
S53 3	684	(thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:13
S53 4	141	(thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) near2 (nanometers or nm or angstrom or ang)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:20
S53 5	20	(thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) near2 (nanometers or nm or angstrom or ang) and ((thick or thickness) near substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:22
S53 6	0	(thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) near2 (nanometers or nm or angstrom or ang) and ((thick or thickness) near substrate near (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:22
S53 7	10	(thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) near2 (nanometers or nm or angstrom or ang) and ((thick or thickness) near2 substrate near2 (nanometer or nm or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:23

S538	436	((thick or thickness) near (substrate) near (angstrom or ang or nanometer or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:24
S539	35	((thick or thickness) near (substrate) near (angstrom or ang or nanometer or nm)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:25
S540	6959	((thick or thickness) near (substrate)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:25
S541	546	((thick or thickness) near (substrate)).clm. and ((thick or thickness) near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:25
S542	152	((thick or thickness) near (substrate)).clm. and ((thick or thickness) near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:27
S543	0	((thick or thickness) near (substrate)).clm. and ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:27
S544	25	((thick or thickness) near (substrate)) same ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:27
S545	21	((thick or thickness) near (substrate)) with ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:29
S546	109	((thick or thickness) near (substrate)) and ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:31

S547	150	((thick or thickness) near (substrate or wafer)) and ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:31
S548	27	((thick or thickness) near (substrate or wafer)) near10 ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:32
S549	444	((thick or thickness) near (substrate or wafer)) near10 ((thick or thickness) near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:34
S550	17089	((thick or thickness or distance) near5 (substrate or wafer)) near10 ((thick or thickness or distance) near5 (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:34
S551	80	((thick or thickness or distance) near5 (substrate or wafer)) near10 ((thick or thickness or distance) near5 (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:36
S552	25	((thick or thickness or distance) near5 (substrate or wafer)) near10 ((thick or thickness or distance) near5 (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping)) and (micrometer or meter or angstrom or ang or nanometer or nm).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:38

| S55 3 | 285 | (US-20010015168-$ or US-20020005562-$ or US-20020121661-$ or US-20020127820-$ or US-20030020068-$ or US-20030080377-$ or US-20030104681-$ or US-20040007741-$ or US-20040032005-$ or US-20050269597-$ or US-20050272207-$ or US-20050272230-$ or US-20020009837-$ or US-20010000411-$ or US-20020142507-$ or US-20020158291-$ or US-20030104658-$ or US-20030211711-$ or US-20040023430-$ or US-20040070051-$ or US-20040145000-$ or US-20040214394-$ or US-20050087811-$ or US-20050116289-$ or US-20050118826-$).did. or (US-3508980-$ or US-3897274-$ or US-3933540-$ or US-4005468-$ or US-4109270-$ or US-4272880-$ or US-4432006-$ or US-4601779-$ or US-4651001-$ or US-4662956-$ or US-4667392-$ or US-4679306-$ or US-4712152-$ or US-4717677-$ or US-4746963-$ or US-4771016-$ or US-4774556-$ or US-4785343-$ or US-4789642-$ or US-4851078-$ or US-4851363-$ or US-4853343-$ or US-4870475-$ or US-4871685-$ or US-4897362-$ or US-4899204-$).did. or (US-4925809-$ or US-4939568-$ or US-4963505-$ or US-4997786-$ or US-5013681-$ or US-5025304-$ or US-5034343-$ or US-5061652-$ or US-5100830-$ or US-5102821-$ or US-5116771-$ or US-5123975-$ or US-5159429-$ or US-5168078-$ or US-5200348-$ or US-5212397-$ or US-5227653-$ or US-5227660-$ or US-5234535-$ or US-5234846-$ or US-5243209-$ or US-5248633-$ or US-5264395-$ or US-5277748-$ or US-5279978-$ or US-5296385-$ or US-5308788-$).did. or (US-5310451-$ or US-5315144-$ or US-5321298-$ or US-5324678-$ or US-5340435-$ or US-5344524-$ or US-5344785-$ or US-5352341-$ or US-5365877-$ or US-5366923-$ or US-5366924-$ or US-5372952-$ or US-5374581-$ or US-5376560-$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2006/01/27 13:38 |

S554	7	S553 and ((semiconductor adj substrate) near2 (thick or thickness)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:43
S555	17	S553 and ((semiconductor adj substrate) near2 (thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:44
S556	917	((semiconductor adj substrate) near2 (thick or thickness)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:44
S557	391	(oxide or insulating or insulation or dielectric or insulator) with ((semiconductor adj substrate) near2 (thick or thickness)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:45
S558	326	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) with ((semiconductor adj substrate) near2 (thick or thickness)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:46
S559	305	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:46
S560	2	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 order).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:47
S561	2	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 (percentage or percen or order)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:47
S562	34	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 (percentage or percen or order))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:47

S56 3	35	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 (percentage or percent or order))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:49
S56 4	3	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 (percentage or percent or order)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:48
S56 5	2	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:49
S56 6	2	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) with ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:49
S56 7	250	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) with ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping or wafer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:50
S56 8	188	((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping or wafer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:50

S56 9	4	(((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping or wafer)))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:51
S57 0	188	(((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping or wafer))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:52
S57 1	1617	(depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near (film or layer))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:54

| S57 2 | 285 | (US-20010015168-$ or US-20020005562-$ or US-20020121661-$ or US-20020127820-$ or US-20030020068-$ or US-20030080377-$ or US-20030104681-$ or US-20040007741-$ or US-20040032005-$ or US-20050269597-$ or US-20050272207-$ or US-20050272230-$ or US-20020009837-$ or US-20010000411-$ or US-20020142507-$ or US-20020158291-$ or US-20030104658-$ or US-20030211711-$ or US-20040023430-$ or US-20040070051-$ or US-20040145000-$ or US-20040214394-$ or US-20050087811-$ or US-20050116289-$ or US-20050118826-$).did. or (US-3508980-$ or US-3897274-$ or US-3933540-$ or US-4005468-$ or US-4109270-$ or US-4272880-$ or US-4432006-$ or US-4601779-$ or US-4651001-$ or US-4662956-$ or US-4667392-$ or US-4679306-$ or US-4712152-$ or US-4717677-$ or US-4746963-$ or US-4771016-$ or US-4774556-$ or US-4785343-$ or US-4789642-$ or US-4851078-$ or US-4851363-$ or US-4853343-$ or US-4870475-$ or US-4871685-$ or US-4897362-$ or US-4899204-$).did. or (US-4925809-$ or US-4939568-$ or US-4963505-$ or US-4997786-$ or US-5013681-$ or US-5025304-$ or US-5034343-$ or US-5061652-$ or US-5100830-$ or US-5102821-$ or US-5116771-$ or US-5123975-$ or US-5159429-$ or US-5168078-$ or US-5200348-$ or US-5212397-$ or US-5227653-$ or US-5227660-$ or US-5234535-$ or US-5234846-$ or US-5243209-$ or US-5248633-$ or US-5264395-$ or US-5277748-$ or US-5279978-$ or US-5296385-$ or US-5308788-$).did. or (US-5310451-$ or US-5315144-$ or US-5321298-$ or US-5324678-$ or US-5340435-$ or US-5344524-$ or US-5344785-$ or US-5352341-$ or US-5357877-$ or US-5366923-$ or US-5366924-$ or US-5372952-$ or US-5374581-$ or US-5376560-$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2006/01/27 13:53 |

S57 3	15	S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near (film or layer))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:55
S57 4	0	S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near (film or layer) near (nm or angstrom or nanometer or ang))). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:55
S57 5	0	S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near2 (film or layer) near (nm or angstrom or nanometer or ang))). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:55
S57 6	0	S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near2 (film or layer) near (nm or angstrom or nanometer or ang)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:55
S57 7	6	S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near2 (film or layer) near2 (nm or angstrom or nanometer or ang)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:56
S57 8	1	S572 and (depth near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:57
S57 9	230	(depth near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 13:57
S58 0	25	(depth near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:26
S58 1	230	(depth near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:27

S58 2	274	((distance or depth) near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:28
S58 3	8288	(distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:33
S58 4	4991	(distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer) and ((thickness or thick) near5 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near5 (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:33
S58 5	2383	(distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer) and ((thickness or thick) near5 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near5 (layer or film)) near5 (angstrom or ang or nanometer or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:34
S58 6	524	(distance or depth) near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near5 (film or layer) and ((thickness or thick) near2 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near2 (layer or film)) near2 (angstrom or ang or nanometer or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:35
S58 7	41	(distance or depth) near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near5 (film or layer) and ((thickness or thick) near2 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near2 (layer or film)) near2 (angstrom or ang or nanometer or nm)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:35

S588	7	((distance or depth) near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near5 (film or layer)).clm. and ((thickness or thick) near2 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near2 (layer or film)) near2 (angstrom or ang or nanometer or nm)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:36
S589	14	((distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer)).clm. and ((thickness or thick) near2 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near2 (layer or film)) near2 (angstrom or ang or nanometer or nm)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:36
S590	131	((distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer)).clm. and ((thickness or thick) near5 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near5 (layer or film)) near5 (angstrom or ang or nanometer or nm)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:37
S591	73	((distance or depth) near10 ((first or second or upper or lower or top or bottom or main or reverse) near surface) near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer)).clm. and ((thickness or thick) near5 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near5 (layer or film)) near5 (angstrom or ang or nanometer or nm)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:39
S592	0	(distance near between near ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near2 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:41

S59 3	0	(distance near between near2 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near2 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:41
S59 4	0	(distance near between near3 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near2 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:41
S59 5	0	(distance near between near3 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near3 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:41
S59 6	0	(distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near3 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:41
S59 7	0	(distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:42
S59 8	173	(distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:43

S59 9	65	(distance near between near2 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near2 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:43
S60 0	70	(distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:44
S60 1	2	(distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near5 (silicon adj substrate)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:45
S60 2	6	(distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near5 (semiconductor adj substrate)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:46
S60 3	9	(distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near5 (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:47
S60 4	27	(distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near10 (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:47

S60 5	0	(distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near10 (buried adj (oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near10 (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:48
S60 6	2	(distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near10 (buried adj (oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near10 (substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:49
S60 7	2	(distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 (buried adj (oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:50
S60 8	49	(distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:50
S60 9	394	((distance or depth) near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:51
S61 0	111	(((distance or depth) near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:51

S61 1		77	(((distance or depth) near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:51
S61 2		45	(((distance or depth) near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:53
S61 3		21	(((distance or depth) near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 ((silicon or semiconductor) adj substrate)) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:55
S61 4		17297	(reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:56
S61 5		4955	(reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:56
S61 6		1	(reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) and 10/602673	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:57

S61 7	30	(reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) and (autodope or autodoping or auto-dope or auto-doping or (auto near dope) or (auto near doping))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 14:57
S61 8	20	(reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) and (autodope or autodoping or auto-dope or auto-doping or (auto near dope) or (auto near doping)) and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:00
S61 9	1533	(reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:02
S62 0	651	(reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)).clm. and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:03
S62 1	97	(reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)).clm. and wafer.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:06

S62 2	1	distance near between near2 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:06
S62 3	11	distance near between near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:08
S62 4	20	distance near between near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:10
S62 5	16	distance near between near5 ((reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface) near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:09
S62 6	193	(depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:10

S627	45	((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:15
S628	34	((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. and (angstrom or ang or nanometer or nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:16
S629	18	((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. and ((angstrom or ang or nanometer or nm) near5 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:17
S630	1	((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. and ((angstrom or ang or nanometer or nm) near5 substrate) and (substrate near (thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:18

S63 1	8	((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. and ((angstrom or ang or nanometer or nm) near5 substrate) and (substrate near2 (thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:18
S63 2	7	("5034335" | "5233218" | "5494846" | "5512501" | "5780888" | "5869386" | "6022765").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/27 15:37

| S63 3 | 289 | (US-20010000411-$ or US-20010015168-$ or US-20020005562-$ or US-20020009837-$ or US-20020121661-$ or US-20020127820-$ or US-20020142507-$ or US-20020158291-$ or US-20030020068-$ or US-20030080377-$ or US-20030104658-$ or US-20030104681-$ or US-20030211711-$ or US-20040007741-$ or US-20040023430-$ or US-20040032005-$ or US-20040070051-$ or US-20040145000-$ or US-20040214394-$ or US-20050087811-$ or US-20050116289-$ or US-20050118826-$ or US-20050269597-$ or US-20050272207-$ or US-20050272230-$).did. or (US-3508980-$ or US-3897274-$ or US-3933540-$ or US-4005468-$ or US-4109270-$ or US-4272880-$ or US-4432006-$ or US-4601779-$ or US-4651001-$ or US-4662956-$ or US-4667392-$ or US-4679306-$ or US-4712152-$ or US-4717677-$ or US-4746963-$ or US-4771016-$ or US-4774556-$ or US-4785343-$ or US-4789642-$ or US-4851078-$ or US-4851363-$ or US-4853343-$ or US-4870475-$ or US-4871685-$ or US-4897362-$ or US-4899204-$).did. or (US-4925809-$ or US-4939568-$ or US-4963505-$ or US-4997786-$ or US-5013681-$ or US-5025304-$ or US-5034343-$ or US-5061652-$ or US-5100830-$ or US-5102821-$ or US-5116771-$ or US-5123975-$ or US-5159429-$ or US-5168078-$ or US-5200348-$ or US-5212397-$ or US-5227653-$ or US-5227660-$ or US-5234535-$ or US-5234846-$ or US-5243209-$ or US-5248633-$ or US-5264395-$ or US-5277748-$ or US-5279978-$ or US-5296385-$ or US-5308788-$).did. or (US-5310451-$ or US-5315144-$ or US-5321298-$ or US-5324678-$ or US-5340435-$ or US-5344524-$ or US-5344785-$ or US-5352341-$ or US-5365877-$ or US-5366923-$ or US-5366924-$ or US-5372952-$ or US-5374581-$ or US-5376560-$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2006/01/27 15:45 |

S634	130	S633 and (substrate near5 (thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:50
S635	29	S633 and (substrate near5 (thick or thickness) near5 (nm or nanometer or micrometer or angstrom or ang))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:53
S636	65	S633 and (substrate near2 (thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 16:00
S637	0	S633 and (substrate near2 (thick or thickness) near2 ".mu.m")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:56
S638	0	S633 and (substrate near2 (thick or thickness) near2 mu)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 15:56
S639	130	S633 and (substrate near5 (thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 16:00